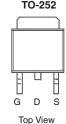
# N-Channel 60 V (D-S) MOSFET

| PRODUCT SUMMARY     |                                   |                                 |  |  |  |
|---------------------|-----------------------------------|---------------------------------|--|--|--|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)           | I <sub>D</sub> (A) <sup>a</sup> |  |  |  |
| 60                  | 0.0018 at V <sub>GS</sub> = 10 V  | 180                             |  |  |  |
|                     | 0.0028 at V <sub>GS</sub> = 4.5 V | 155                             |  |  |  |



- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

D

S

N-Channel MOSFET

| Parameter  | Symbol                  | Limit                             | Unit             |    |  |
|--|-------------------------|-----------------------------------|------------------|----|--|
| Gate-Source Voltage  | V <sub>GS</sub>         | ± 20                              | V                |    |  |
| Continuous Drain Current (T <sub>.1</sub> = 175 °C) <sup>b</sup> | T <sub>C</sub> = 25 °C  | I-                                | 180              |    |  |
| Continuous Drain Current $(T_J = 175^{\circ}C)^2$                | T <sub>C</sub> = 100 °C | I <sub>D</sub>                    | 135 <sup>a</sup> |    |  |
| Pulsed Drain Current   | I <sub>DM</sub>         | 720                               | А                |    |  |
| Continuous Source Current (Diode Conduction)                     | ۱ <sub>S</sub>          | 180 <sup>a</sup>                  |                  |    |  |
| Avalanche Current  | I <sub>AS</sub>         | 150                               |                  |    |  |
| Single Avalanche Energy (Duty Cycle $\leq$ 1 %)                  | L = 0.1 mH              | E <sub>AS</sub>                   | 330              | mJ |  |
| Maximum Power Dissipation  | T <sub>C</sub> = 25 °C  | P <sub>D</sub>                    | 255              | w  |  |
| Maximum rower Dissipation  | T <sub>A</sub> = 25 °C  | 'D                                | 6.9 <sup>b</sup> | V  |  |
| Operating Junction and Storage Temperature Range                 |                         | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 175      | °C |  |

| THERMAL RESISTANCE RATINGS               |                        |                   |         |      |      |  |
|--|------------------------|-------------------|---------|------|------|--|
| Parameter                                | Symbol                 | Typical           | Maximum | Unit |      |  |
| Maximum hungting to Ambient              | $t \le 10 \text{ sec}$ | R <sub>thJA</sub> | 8       | 15   |      |  |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State           |                   | 12      | 45   | °C/W |  |
| Maximum Junction-to-Case                 |                        | R <sub>thJC</sub> | 0.9     | 1.5  |      |  |

Notes:

a. Package limited.

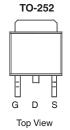
b. Surface mounted on 1" x 1" FR4 board.

c. t  $\leq$  10 s.



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| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |  |      |                   |        |      |  |
|---|---------------------|--|------|-------------------|--------|------|--|
| Parameter   | Symbol              | Test Conditions  | Min. | Typ. <sup>a</sup> | Max.   | Unit |  |
| Static  |                     |  |      |                   |        |      |  |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>     | $V_{GS} = 0 V, I_{D} = 250 \mu A$  | 60   |                   |        | v    |  |
| Gate Threshold Voltage  | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$   | 1    | -                 | 3      |      |  |
| Gate-Body Leakage   | I <sub>GSS</sub>    | $V_{DS} = 0 V, V_{GS} = \pm 20 V$  |      |                   | ± 100  | nA   |  |
|   |                     | $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$  | 1    |                   | 1      |      |  |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>    | $V_{DS} = 48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$            |      |                   | 50     | μA   |  |
|   |                     | $V_{DS} = 48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 \text{ °C}$            |      |                   | 250    |      |  |
| On-State Drain Current <sup>b</sup>                             | I <sub>D(on)</sub>  | $V_{DS} = 5 V, V_{GS} = 10 V$  | 180  |                   |        | А    |  |
|   |                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A  |      | 0.0018            | 0.0026 | 2 Ω  |  |
|   | P                   | $V_{GS}$ = 10 V, I <sub>D</sub> =20 A, T J = 125 °C  |      | 0.0023            | 0.0032 |      |  |
| Drain-Source On-State Resistance <sup>b</sup>                   | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> =15 A, T <sub>J</sub> = 175 °C                            |      | 0.0029            | 0.0042 |      |  |
|   |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A   |      | 0.0028            | 0.0039 |      |  |
| Forward Transconductance <sup>b</sup>                           | 9 <sub>fs</sub>     | $V_{DS} = 48 \text{ V}, I_{D} = 20 \text{ A}$  |      | 175               |        | S    |  |
| Dynamic   |                     |  |      |                   |        |      |  |
| Input Capacitance   | C <sub>iss</sub>    |  |      | 11050             |        | pF   |  |
| Output Capacitance  | C <sub>oss</sub>    | $V_{GS}$ = 0 V, $V_{DS}$ = 48 V, f = 1 MHz   |      | 1650              |        |      |  |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>    |  |      | 185               |        |      |  |
| Total Gate Charge <sup>c</sup>                                  | Qg                  |  |      | 79                |        |      |  |
| Gate-Source Charge <sup>c</sup>                                 | Q <sub>gs</sub>     | $V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$                               |      | 16                |        | nC   |  |
| Gate-Drain Charge <sup>c</sup>                                  | Q <sub>gd</sub>     |  |      | 20                |        |      |  |
| Turn-On Delay Time <sup>c</sup>                                 | t <sub>d(on)</sub>  |  |      | 20                |        |      |  |
| Rise Time <sup>c</sup>  | t <sub>r</sub>      | $V_{DD}$ = 48 V, $R_L$ = 0.6 $\Omega$  |      | 35                |        | ns   |  |
| Turn-Off Delay Time <sup>c</sup>                                | t <sub>d(off)</sub> | $\text{I}_\text{D} \cong$ 20 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 2.5 $\Omega$ |      | 68                |        |      |  |
| Fall Time <sup>c</sup>  | t <sub>f</sub>      |  |      | 15                |        |      |  |
| Source-Drain Diode Ratings and Ch                               | aracteristics (     | T <sub>C</sub> = 25 °C)  |      |                   |        |      |  |
| Pulsed Current  | I <sub>SM</sub>     |  |      |                   | 720    | А    |  |
| Diode Forward Voltage   | $V_{SD}$            | $I_{F} = 20 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$   |      |                   | 1.25   | V    |  |
| Reverse Recovery Time   | t <sub>rr</sub>     | I <sub>F</sub> = 20 A, di/dt = 100 A/µs  |      | 73                |        | ns   |  |

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

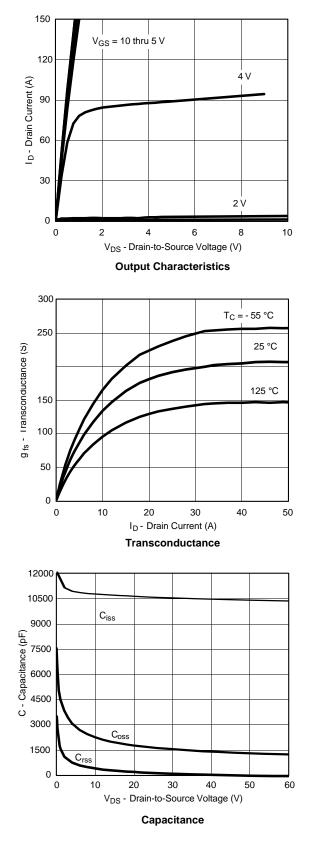
c. Independent of operating temperature.

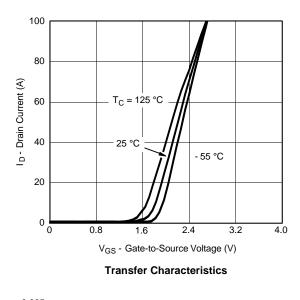
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

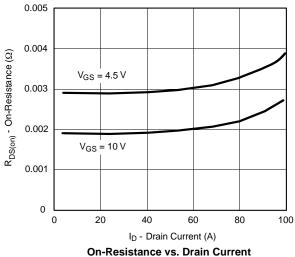


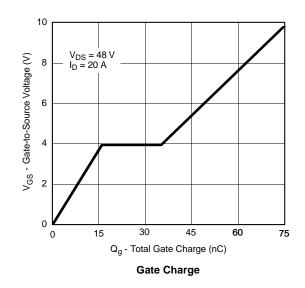
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#### TYPICAL CHARACTERISTICS (25 °C unless noted)





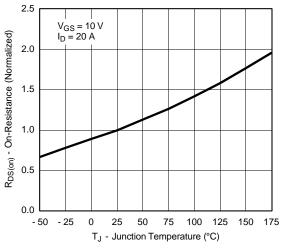




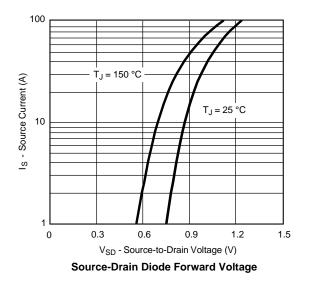


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#### TYPICAL CHARACTERISTICS (25 °C unless noted)



**On-Resistance vs. Junction Temperature** 

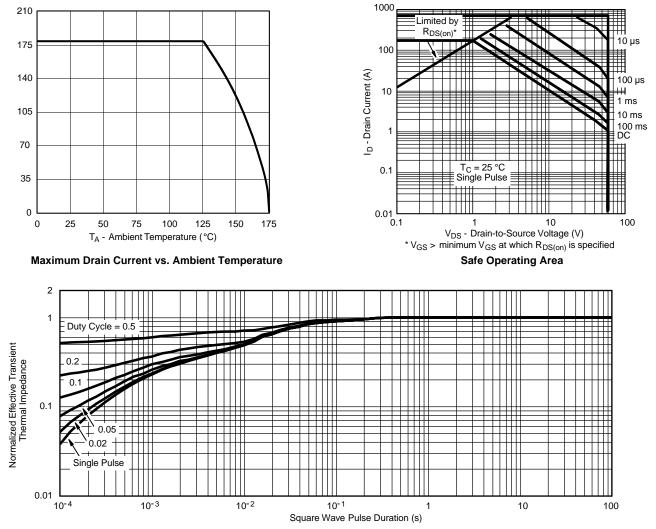




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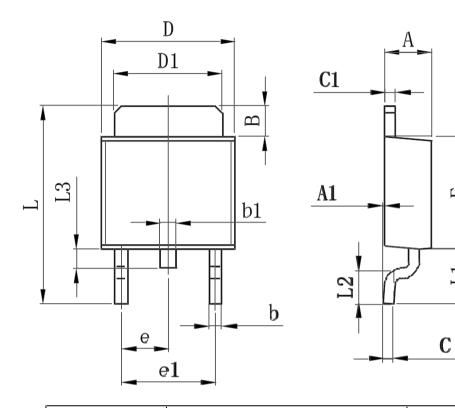
#### THERMAL RATINGS

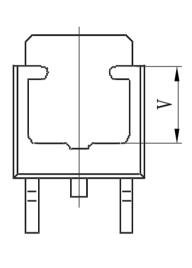


Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-252-2L PACKAGE OUTLINE DIMENSIONS**





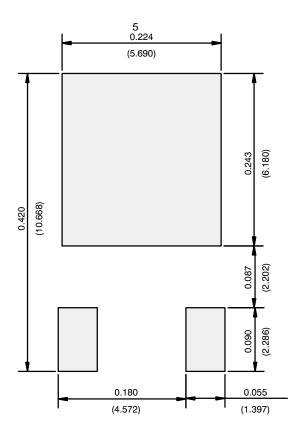
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| Symbol | Dimensions | In Millimeters      | Dimensions In Inches |       |  |
|--------|------------|---------------------|----------------------|-------|--|
| Symbol | Min.       | Max.                | Min.                 | Max.  |  |
| A      | 2.200      | 2.400               | 0.087                | 0.094 |  |
| A1     | 0.000      | 0.127               | 0.000                | 0.005 |  |
| В      | 1.350      | 1.650               | 0.053                | 0.065 |  |
| b      | 0.500      | 0.700               | 0.020                | 0.028 |  |
| b1     | 0.700      | 0.900               | 0.028                | 0.035 |  |
| С      | 0.430      | 0.580               | 0.017                | 0.023 |  |
| c1     | 0.430      | 0.580               | 0.017                | 0.023 |  |
| D      | 6.350      | 6.650               | 0.250                | 0.262 |  |
| D1     | 5.200      | 5.400               | 0.205                | 0.213 |  |
| E      | 5.400      | 5.700               | 0.213                | 0.224 |  |
| е      | 2.300      | 2.300 TYP.          |                      | TYP.  |  |
| e1     | 4.500      | 4.700               | 0.177                | 0.185 |  |
| L      | 9.500      | 9.900               | 0.374                | 0.390 |  |
| L1     | 2.550      | 2.900               | 0.100                | 0.114 |  |
| L2     | 1.400      | 1 <sup>1</sup> .780 | 0.055                | 0.070 |  |
| L3     | 0.600      | 0.900               | 0.024                | 0.035 |  |
| V      | 3.800      | REF.                | 0.150 REF.           |       |  |



#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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